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November 1999

## FAIRCHILD

## FDN339AN N-Channel 2.5V Specified PowerTrench® MOSFET

#### **General Description**

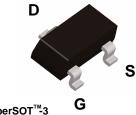
This N-Channel 2.5V specified MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

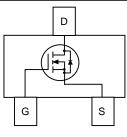
#### Applications

- DC/DC converter
- Load switch

### Features

- 3 A, 20 V.  $\rm R_{\rm DS(ON)}$  = 0.035  $\Omega~@~\rm V_{\rm GS}$  = 4.5 V  $R_{DS(ON)} = 0.050 \ \Omega \ @ V_{GS} = 2.5 \ V.$
- Low gate charge (7nC typical).
- High performance trench technology for extremely low R<sub>DS(ON)</sub>.
- High power and current handling capability.





#### SuperSOT<sup>™</sup>-3

## Absolute Maximum Ratings $T_A = 25^{\circ}C$ unless otherwise noted

| Symbol                            | Parameter  |           | Ratings     | Units |
|-----------------------------------|--|-----------|-------------|-------|
| V <sub>DSS</sub>                  | Drain-Source Voltage                             |           | 20          | V     |
| V <sub>GSS</sub>                  | Gate-Source Voltage                              |           | ±8          | V     |
| I <sub>D</sub>                    | Drain Current - Continuous                       | (Note 1a) | 3           | A     |
|                                   | - Pulsed   |           | 20          |       |
| P <sub>D</sub>                    | Power Dissipation for Single Operation           | (Note 1a) | 0.5         | W     |
|                                   |  | (Note 1b) | 0.46        |       |
| T <sub>J</sub> , T <sub>stg</sub> | Operating and Storage Junction Temperature Range |           | -55 to +150 | °C    |

## **Thermal Characteristics**

| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | (Note 1a) | 250 | °C/W |
|-----------------|---|-----------|-----|------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case    | (Note 1)  | 75  | °C/W |

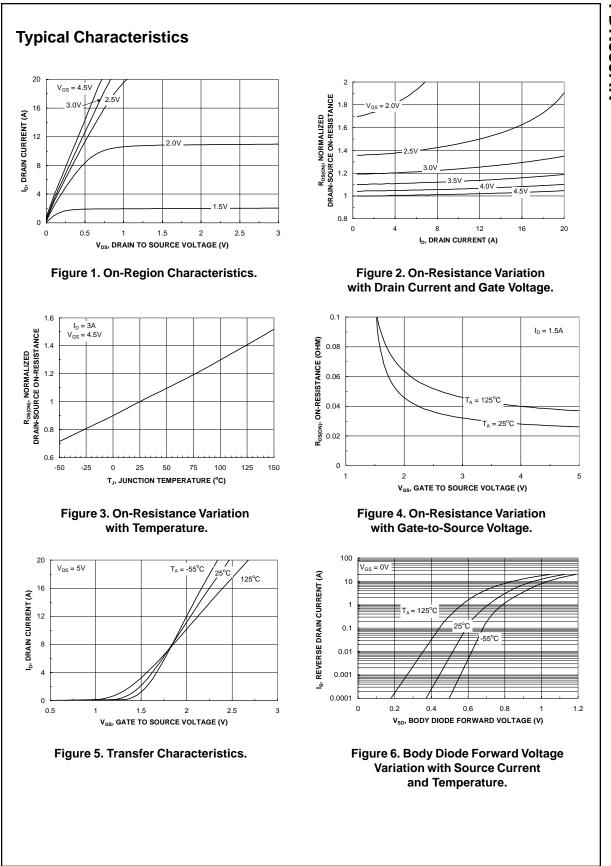
## **Package Outlines and Ordering Information**

| Device Marking | Device   | Reel Size | Tape Width | Quantity |
|----------------|----------|-----------|------------|----------|
| 339            | FDN339AN | 7"        | 8mm 3      |          |

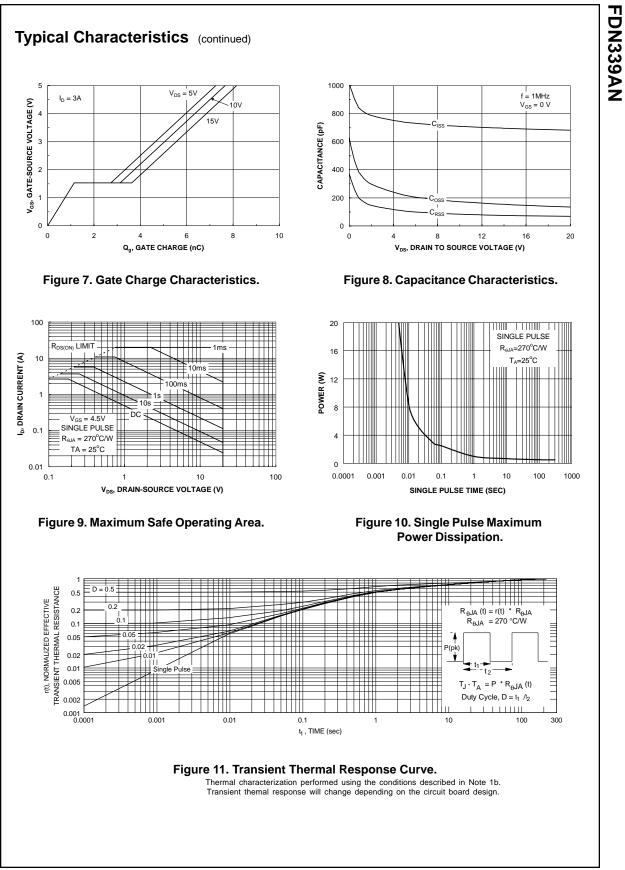
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| Symbol                                 | Parameter   | Test Conditions   | Min | Тур                     | Max                     | Units    |
|--|---|---|-----|-------------------------|-------------------------|----------|
| Off Char                               | acteristics   |   |     |                         |                         |          |
| BV <sub>DSS</sub>                      | Drain-Source Breakdown Voltage                                      | $V_{GS} = 0 V, I_D = 250 \mu A$   | 20  |                         |                         | V        |
| <u>ΔBVdss</u><br>ΔTj                   | Breakdown Voltage Temperature<br>Coefficient                        | $I_D = 250 \ \mu\text{A}, \text{Referenced to } 25^{\circ}\text{C}$   |     | 14                      |                         | mV/°C    |
| I <sub>DSS</sub>                       | Zero Gate Voltage Drain Current                                     | $V_{DS} = 16 V, V_{GS} = 0 V$   |     |                         | 1                       | μΑ       |
| I <sub>GSSF</sub>                      | Gate-Body Leakage Current,<br>Forward                               | V <sub>GS</sub> = 8 V, V <sub>DS</sub> = 0 V  |     |                         | 100                     | nA       |
| I <sub>GSSR</sub>                      | Gate-Body Leakage Current,<br>Reverse                               | $V_{GS} = -8 \text{ V},  V_{DS} = 0 \text{ V}$  |     |                         | -100                    | nA       |
| On Char                                | acteristics (Note 2)  |   |     |                         |                         |          |
| V <sub>GS(th)</sub>                    | Gate Threshold Voltage  | $V_{DS} = V_{GS}, I_D = 250 \ \mu A$  | 0.4 | 0.85                    | 1.5                     | V        |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate Threshold Voltage<br>Temperature Coefficient                   | $I_D = 250 \ \mu\text{A}, \text{Referenced to } 25^\circ\text{C}$   |     | -3                      |                         | mV/°C    |
| R <sub>DS(on)</sub>                    | Static Drain-Source<br>On-Resistance                                |   |     | 0.029<br>0.040<br>0.039 | 0.035<br>0.061<br>0.050 | Ω        |
| I <sub>D(on)</sub>                     | On-State Drain Current  | $V_{GS} = 4.5 \text{ V}, V_{DS} = 5 \text{ V}$  | 10  | 0.000                   | 0.000                   | Α        |
| <b>g</b> FS                            | Forward Transconductance  | $V_{DS} = 5 V, I_D = 3 A$   |     | 11                      |                         | S        |
| Dunamia                                | Characteristics   |   |     |                         |                         |          |
|  | Input Capacitance   | $V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0 \text{ V},$  |     | 700                     | Ì                       | pF       |
|  | Output Capacitance  | f = 1.0  MHz  |     | 175                     |                         | pF       |
| Crss                                   | Reverse Transfer Capacitance  | -   |     | 85                      |                         | pF       |
|  | ·   |   |     |                         |                         | 1.       |
|  | Characteristics (Note 2)  |   |     | 0                       | 40                      |          |
| t <sub>d(on)</sub>                     | Turn-On Delay Time<br>Turn-On Rise Time                             | $V_{DD} = 10 \text{ V}, \text{ I}_D = 1 \text{ A},$<br>$V_{GS} = 4.5 \text{ V}, \text{ R}_{GEN} = 6 \Omega$ |     | 8                       | 16                      | ns       |
| t <sub>r</sub>                         |   | $v_{\rm GS} = 4.5 v, r_{\rm GEN} = 0.22$  |     | 10                      | 18                      | ns       |
| t <sub>d(off)</sub>                    | Turn-Off Delay Time<br>Turn-Off Fall Time                           | 4   |     | 18                      | 29<br>10                | ns       |
| t <sub>f</sub>                         |   | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 3 A,   |     | 5<br>7                  | 10                      | ns<br>nC |
| Q <sub>g</sub>                         | Total Gate Charge<br>Gate-Source Charge                             | $V_{DS} = 10$ V, $I_{D} = 3$ A,<br>$V_{GS} = 4.5$ V   |     | 1.2                     | 10                      | nC       |
| Q <sub>gs</sub>                        | ě   |   |     | 1.2                     |                         | nC       |
| Q <sub>gd</sub>                        | Gate-Drain Charge   |   |     | 1.9                     |                         | nc       |
| Drain-Sc                               | urce Diode Characteristics a  | nd Maximum Ratings  |     |                         |                         |          |
| le le                                  | Maximum Continuous Drain-Source D                                   | Diode Forward Current   |     |                         | 0.42                    | Α        |
| I <sub>S</sub><br>V <sub>SD</sub>      | Drain-Source Diode Forward Voltage                                  | $V_{GS} = 0 V, I_S = 0.42 A$ (Note  |     | 0.65                    | 1.2                     | V        |
| Drain-Sc                               | purce Diode Characteristics an<br>Maximum Continuous Drain-Source D | Diode Forward Current   |     | 0.65                    |                         |          |

FDN339AN



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|--------------------------|---------------------------|---|
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